

Abstract of the Disclosure

A method for manufacturing a semiconductor device includes the steps of forming a first insulating film on a substrate, forming a
5 second insulating film on the first insulating film, and forming a gate electrode on the second insulating film. The step of forming a second insulating film has a first step of supplying film-forming materials and making the film-forming materials adsorbed on the first insulating film, a second step of purging the film-forming materials
10 that has not been adsorbed, a third step of supplying oxidants to oxidize the adsorbed film-forming materials, and a fourth step of purging the oxidants that has not contributed to oxidization. The step of forming a second insulating film is repeated for a plurality of cycles continuously, and the purging time in the fourth step in the initial
15 predetermined number of cycles is made longer than the purging time in the fourth step in following cycles.